

深圳市晶泰源电子有限公司

2SB649/2SB649A TRANSISTOR (PNP)

FEATURES

Low frequency power amplifier complementary pair
with 2SD669/A

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

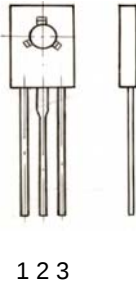
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage		
	2SB649	-120	V
	2SB649A	-160	
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-1.5	A
P_C	Collector Power Dissipation	1	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

TO- 126

1. EMITTER

2. COLLECTOR

3. BASE



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-120			V
		2SB649	-160			
		2SB649A				
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -160\text{V}, I_E = 0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-10	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$	60		320	
	$h_{FE(2)}$	$V_{CE} = -5\text{V}, I_C = -500\text{mA}$	30		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -150\text{mA}$		140		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		27		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range 2SB649	60-120	100-200	160-320
2SB649A	60-120	100-200	